



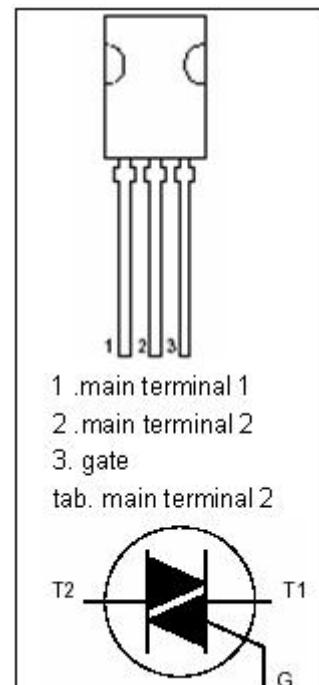
INCHANGE Semiconductor

**isc Triacs****BT134****FEATURES**

- With TO-126P package
- Designed for use in general purpose bidirectional switching and phase control applications , which are intended to be interfaced directly to microcontrollers , logic integrated circuits and other low power gate trigger circuits.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

| SYMBOL                      | PARAMETER                             | MIN     | UNIT |
|-----------------------------|---------------------------------------|---------|------|
| V <sub>DRM</sub>            | Repetitive peak off-state voltage     | 600     | V    |
| V <sub>R<sub>RM</sub></sub> | Repetitive peak off-state voltage     | 600     | V    |
| I <sub>T(RMS)</sub>         | RMS on-state current (full sine wave) | 4       | A    |
| I <sub>TSM</sub>            | Non-repetitive peak on-state current  | 25      | A    |
| P <sub>GM</sub>             | Peak gate power dissipation           | 5       | W    |
| P <sub>G(AV)</sub>          | Average gate power dissipation        | 0.5     | W    |
| T <sub>j</sub>              | Operating junction temperature        | 125     | °C   |
| T <sub>stg</sub>            | Storage temperature                   | -45~150 | °C   |

**ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise specified)**

| SYMBOL                      | PARAMETER                         | CONDITIONS  | MIN | MAX         | UNIT |
|-----------------------------|-----------------------------------|---|-----|-------------|------|
| I <sub>R<sub>RM</sub></sub> | Repetitive peak reverse current   | V <sub>R</sub> =V <sub>R<sub>RM</sub></sub> ,<br>V <sub>R</sub> =V <sub>R<sub>RM</sub></sub> , T <sub>j</sub> =125 °C |     | 0.01<br>0.2 | mA   |
| I <sub>D<sub>RM</sub></sub> | Repetitive peak off-state current | V <sub>D</sub> =V <sub>DRM</sub> ,<br>V <sub>D</sub> =V <sub>DRM</sub> , T <sub>j</sub> =125 °C                       |     | 0.01<br>0.2 | mA   |
| I <sub>GT</sub>             | Gate trigger current              | I   |     | 35          | mA   |
|                             |                                   | II  |     | 35          |      |
|                             |                                   | III   |     | 35          |      |
|                             |                                   | IV  |     | 70          |      |
| V <sub>T<sub>M</sub></sub>  | On-state voltage                  | I <sub>T</sub> = 5A   |     | 1.7         | V    |
| I <sub>H</sub>              | Holding current                   | I <sub>GT</sub> = 0.1A, V <sub>D</sub> = 12V  |     | 10          | mA   |
| V <sub>G<sub>T</sub></sub>  | Gate trigger voltage              | V <sub>D</sub> =12V; I <sub>T</sub> = 0.1A  |     | 1.5         | V    |